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FTB1F-15F THRU FTB10F-15F
1.5A SURFACE MOUNT GLASS PASSIVATED BRIDGE RECTIFIER

Features:

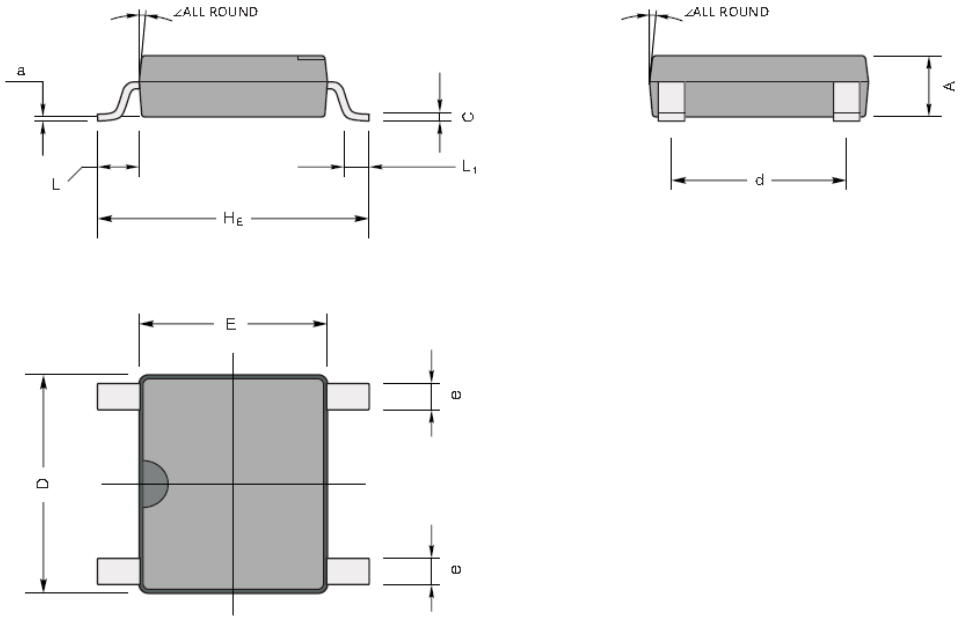
- **Glass Passivated Chip Junction**
- **Reverse Voltage - 100 to 1000 V**
- **Forward Current - 1.5 A**
- **Designed for Surface Mount Application**
- **Fast reverse recovery time**
- **This is a Halogen Free Device**
- **All SMC parts are traceable to the wafer lot**
- **Additional testing can be offered upon request**

PIN	DESCRIPTION
1	Input Pin（~）
2	Input Pin（~）
3	Output Anode（+）
4	Output Cathode（-）

Mechanical Data:

- **Case: ABF**
- **Terminals: Solderable per MIL-STD-750, Method 2026**
- **Weight: 82 mg**

Mechanical Dimensions: In mm/mil



UNIT		A	C	D	E	H_E	d	e	L	L_1	a	∠
mm	max	1.2	0.22	5.2	4.5	6.4	4.2	0.7	0.95	0.6	0.2	7°
	min	1.0	0.15	4.9	4.2	6.0	3.8	0.5				
mil	max	47	8.7	205	177	252	165	28	37	24	4	
	min	39	5.9	193	166	236	150	20				

ABF

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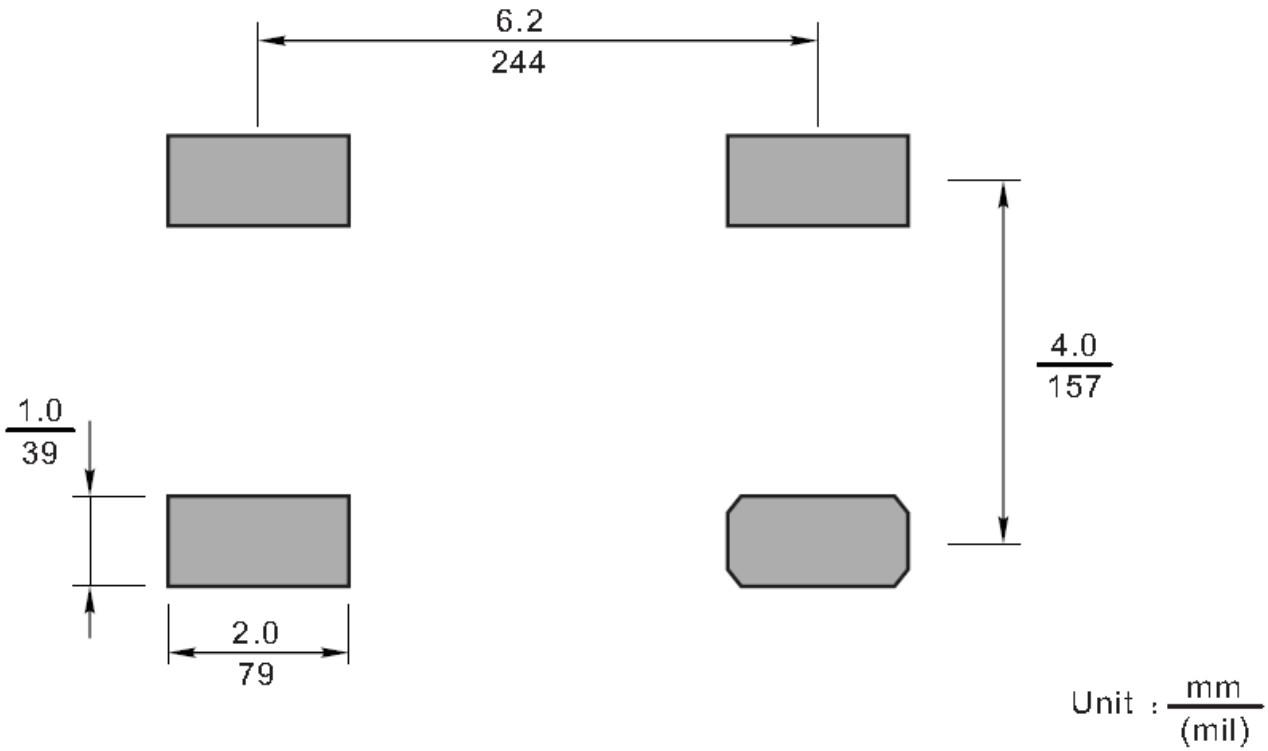
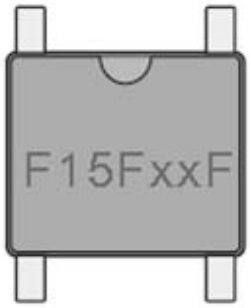
The recommended mounting pad size:



Marking Diagram:

Type number	Marking code
FTB1F-15F	F15F1F
FTB2F-15F	F15 F2F
FTB4F-15F	F15F4F
FTB6F-15F	F15F6F
FTB8F-15F	F15F8F
FTB10F-15F	F15F10F



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Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	FTB1F -15F	FTB2F -15F	FTB4F -15F	FTB6F -15F	FTB8F -15F	FTB10F -15F	Units
Maximum repetitive peak reverse voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	800	1000	V
Average Rectified Output Current at T_A=50℃	I_o	1.5						A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50						A
Maximum instantaneous forward voltage at 1.5A	V_F	1.3						V
Maximum DC reverse current T_A=25 ℃ at rated DC blocking voltage T_A=125 ℃	I_R	5.0 100						μA
Typical Junction Capacitance (Note 1)	C_J	25						pF
Typical Thermal Resistance (Note 2)	$R_{\theta JA}$	80						°C/W
Maximum Reverse Recovery Time (Note 3)	T_{rr} $T_{rr(TYP.)}$	500 300						ns
Junction Temperature	T_J	-55 to +150						°C
Storage Temperature Range	T_{STG}	-55 to +150						°C

Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
2. Mounted on glass epoxy PC board with 4×(5×5mm^2) copper pad.
3. Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

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Fig.1 Average Rectified Output Current Derating Curve

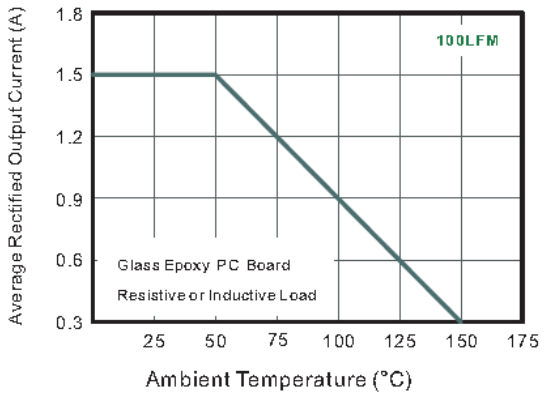


Fig.2 Typical Reverse Characteristics

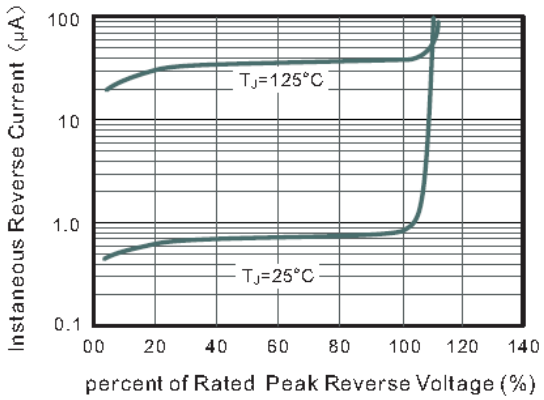


Fig.3 Typical Instaneous Forward Characteristics

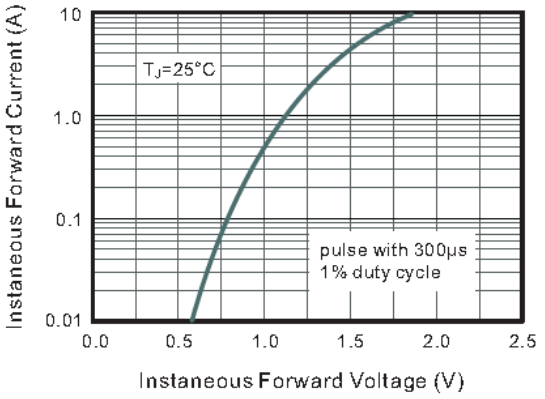


Fig.4 Typical Junction Capacitance

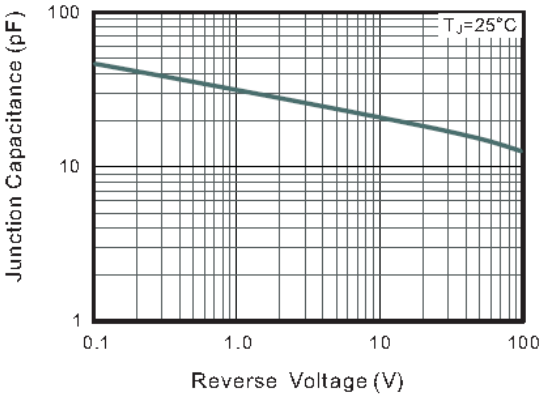
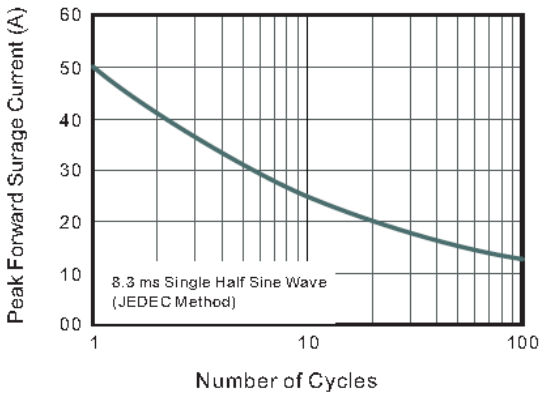


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current



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